Electronic Supplementary Information for

Unraveling the Influence of Substrate Surface and Temperature on Microstructural

Evolution of Crystalline MoS₂ in Atomic Layer Deposition

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Figure S1. Schematics of (a) mica and (b) MoS₂ structures.



Figure S2. Contact angle measurements of (a) the ALD-grown Al₂O₃ and (b) SiO₂ substrates



Figure S3. Raman spectra of MoS₂ grown on (a) Al₂O₃, (b) SiO₂, and (c) mica at 650 °C



Figure S4. AFM images and height profiles of the MoS_2 grown on (a) SiO_2 and (b) Al_2O_3 at 650 °C



Figure S5. AFM images of (a) SiO₂, (b) Al₂O₃, and (c) mica substrates.



Figure S6. Θ -2 Θ theta XRD patterns of the MoS₂ grown on (a) the ALD-grown Al₂O₃ and (b) the mica. Rocking curves of the MoS₂ grown on (c) the ALD-grown Al₂O₃ and (d) the mica.



Figure S7. In-plane φ -scans of the (060) mica and (11 $\overline{2}$ 0) MoS₂ reflections. (b) Schematic of possible coincidence site lattices for MoS₂ domains on mica.